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## FDS6990AS Dual 30V N-Channel PowerTrench<sup>®</sup> SyncFET™

## Features

- 7.5 A, 30 V.  $R_{DS(ON)} = 22 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$  $R_{DS(ON)} = 28 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- Includes SyncFET Schottky diode
- Low gate charge (10nC typical)
- High performance trench technology for extremely low R<sub>DS(ON)</sub>
- High power and current handling capability

## Applications

- DC/DC converter
- Motor drives



D1

D2

Pin 1

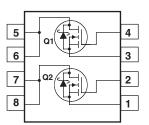
D2

**SO-8** 

## **General Description**

The FDS6990AS is designed to replace a dual SO-8 MOSFET and two Schottky diodes in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low  $R_{DS(ON)}$  and low gate charge. Each MOSFET includes integrated Schottky diodes using Fairchild's monolithic SyncFET technology. The performance of the FDS6990AS as the low-side switch in a synchronous rectifier is similar to the performance of the FDS6990A in parallel with a Schottky diode.

March 2010



### Absolute Maximum Ratings TA=25°C unless otherwise noted

S2

G2

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		30	V
V <sub>GSS</sub>	Gate-Source Voltage		±20	V
I <sub>D</sub>	Drain Current – Continuous	(Note 1a)	7.5	А
	- Pulsed		20	
P <sub>D</sub>	Power Dissipation for Dual Operation		2	W
	Power Dissipation for Single Operation	(Note 1a)	1.6	
		(Note 1b)	1	
		(Note 1c)	0.9	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C
Thermal Cha	aracteristics			
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

## Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6990AS	FDS6990AS	13"	12mm	2500 units

FDS6990AS
Dual 30V
<b>N-Channel</b>
Dual 30V N-Channel PowerTrench <sup>®</sup>
<sup>®</sup> SyncFET™

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Charac	teristics	1	ļ			
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 1 mA$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D = 1$ mA, Referenced to $25^{\circ}C$		31		mV/°C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			500	μA
GSS	Gate-Body Leakage	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA
On Charac	teristics (Note 2)	-	ł	1	1	ł
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1 \text{ mA}$	1	1.7	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 1 \text{ mA}, \text{ Referenced to } 25^{\circ}\text{C}$		-3		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 7.5 \text{ A}$ $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 7.5 \text{ A}, \text{ T}_{J} = 125^{\circ}\text{C}$ $V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 6.5 \text{ A}$		17 26 21	22 35 28	mΩ
D(on)	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	20			Α
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 15 \text{ V}, I_{D} = 10 \text{ A}$		29		S
Dynamic C	haracteristics	-	ł	1	1	
C <sub>iss</sub>	Input Capacitance $V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$			550		pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		162		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			60		pF
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> = 15 mV, f = 1.0 MHz		3.1		Ω
Switching	Characteristics (Note 2)	1	1			
t <sub>d(on)</sub>	Turn–On Delay Time	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 1 A,		8	16	ns
t <sub>r</sub>	Turn–On Rise Time	$V_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		5	10	ns
t <sub>d(off)</sub>	Turn–Off Delay Time	_		24	38	ns
t <sub>f</sub>	Turn–Off Fall Time	_		4	8	ns
t <sub>d(on)</sub>	Turn–On Delay Time	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 1 \text{ A},$		9	18	ns
t <sub>r</sub>	Turn–On Rise Time	$V_{GS}$ = 4.5 V, $R_{GEN}$ = 6 $\Omega$		8	16	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			14	24	ns
t <sub>f</sub>	Turn–Off Fall Time	_		5	10	ns
Q <sub>g(TOT)</sub>	Total Gate Charge at Vgs = 10V	$V_{DD} = 15 \text{ V}, \text{ I}_{D} = 10 \text{ A}, \text{ V}_{GS} = 5 \text{ V}$		10	14	nC
Qg	Total Gate Charge at Vgs = 5V			6	8	nC
Q <sub>gs</sub>	Gate-Source Charge			1.5		nC
Q <sub>gd</sub>	Gate-Drain Charge			2.0		nC
Drain-Sou	rce Diode Characteristics and Maxi	mum Ratings				1
S	Maximum Continuous Drain-Source	Diode Forward Current			2.9	Α
/ <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 V, I_S = 2.3 A$ (Note 2)		0.6	0.7	V
rr	Diode Reverse Recovery Time	I <sub>F</sub> = 10A,		18		nS
Q <sub>rr</sub>	Diode Reverse Recovery Charge	$d_{iF}/d_t = 300 \text{ A/}\mu\text{s} $ (Note 3)		11		nC

#### Notes:

1. R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>BJC</sub> is guaranteed by design while R<sub>BCA</sub> is determined by the user's board design.



a) 78°C/W when mounted on a 0.5 in<sup>2</sup> pad of 2 oz copper

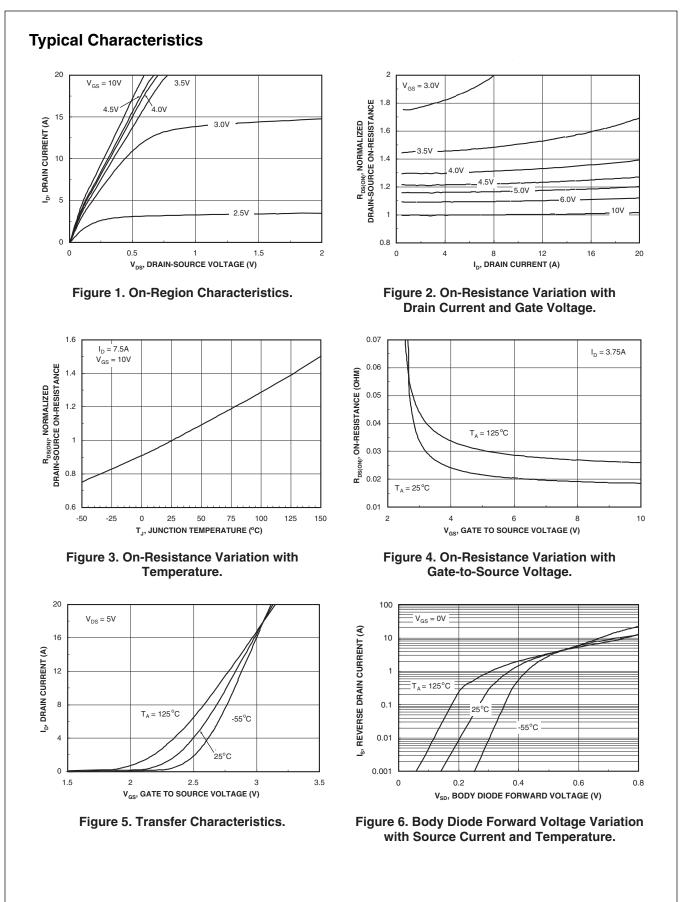


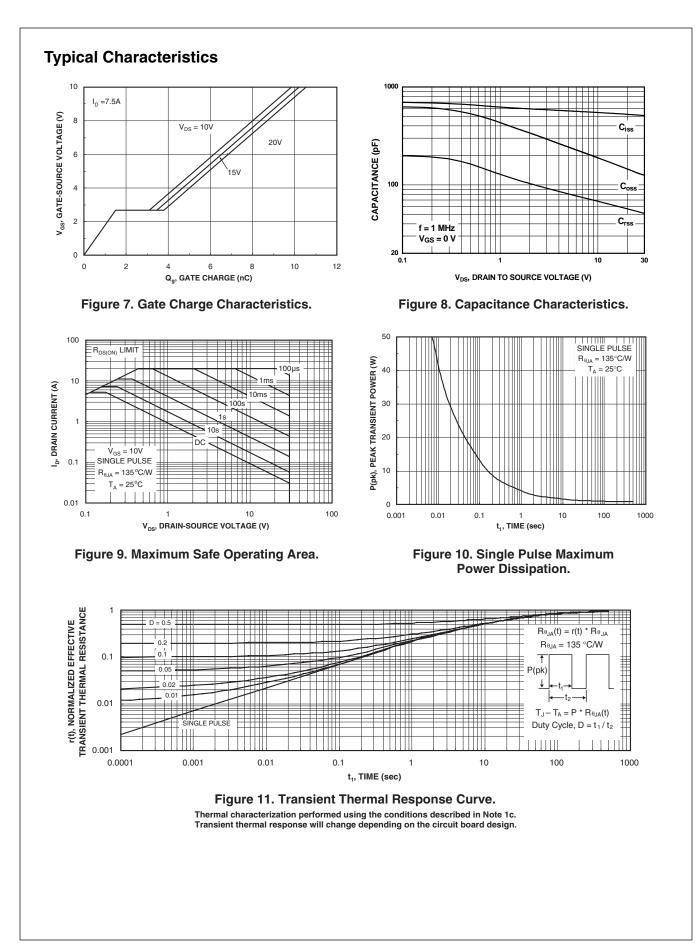
 b) 125°C/W when mounted on a 0.02 in<sup>2</sup> pad of 2 oz copper

c) 135°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

- 2. Pulse Test: Pulse Width < 300 $\mu$ s, Duty Cycle < 2.0%
- 3. See "SyncFET Schottky body diode characteristics" below.

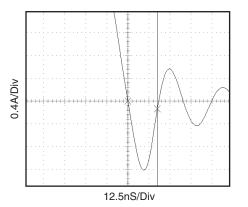




## Typical Characteristics (continued)

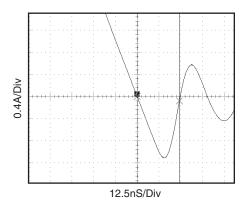
### SyncFET Schottky Body Diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 12 shows the reverse recovery characteristic of the FDS6990AS.



# Figure 12. FDS6990AS SyncFET body diode reverse recovery characteristic.

For comparison purposes, Figure 13 shows the reverse recovery characteristics of the body diode of an equivalent size MOSFET produced without SyncFET (FDS6990A).





Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

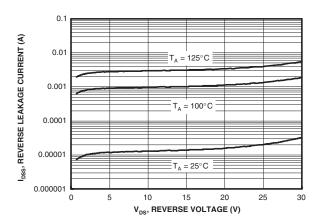
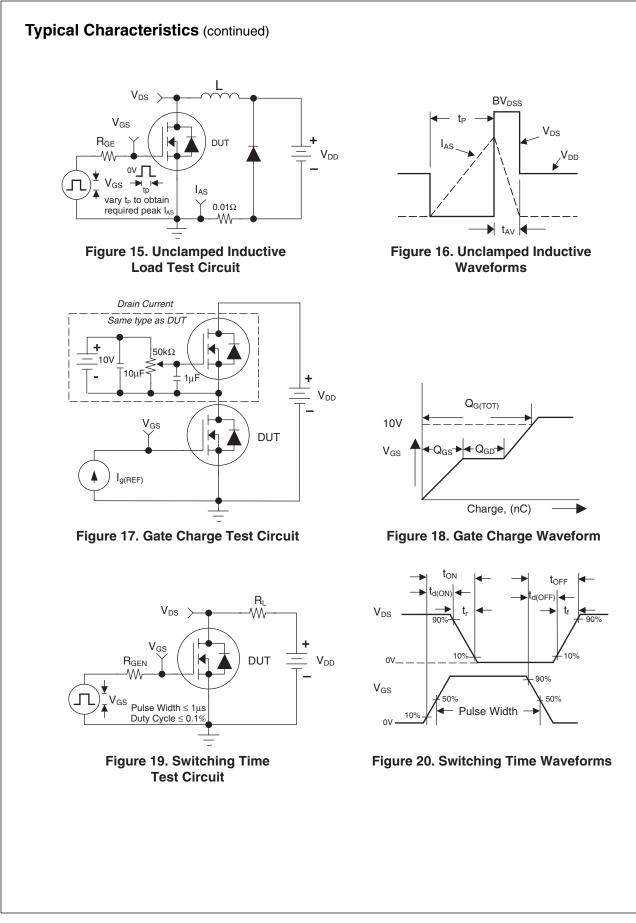
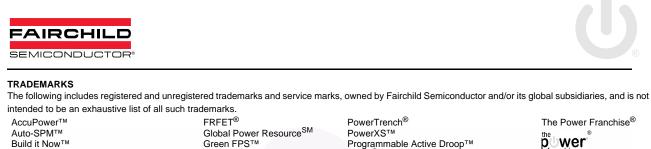


Figure 14. SyncFET body diode reverse leakage versus drain-source voltage and temperature.





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